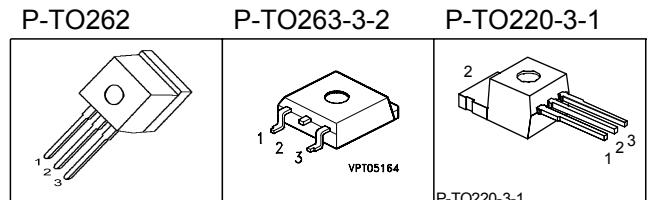


**Cool MOS™ Power Transistor**

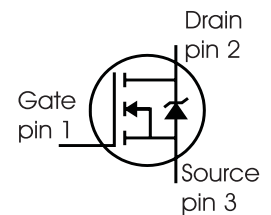
**Feature**

- New revolutionary high voltage technology
- Ultra low gate charge
- Periodic avalanche rated
- Extreme dv/dt rated
- Ultra low effective capacitances
- Improved transconductance

$V_{DS}$	600	V
$R_{DS(on)}$	0.38	$\Omega$
$I_D$	11	A



Type	Package	Ordering Code	Marking
SPP11N60S5	P-TO220-3-1	Q67040-S4198	11N60S5
SPB11N60S5	P-TO263-3-2	Q67040-S4199	11N60S5
SPI11N60S5	P-TO262	Q67040-S4338	11N60S5



**Maximum Ratings**

Parameter	Symbol	Value	Unit
Continuous drain current $T_C = 25\text{ }^\circ\text{C}$ $T_C = 100\text{ }^\circ\text{C}$	$I_D$	11 7	A
Pulsed drain current, $t_p$ limited by $T_{jmax}$	$I_D$ puls	22	
Avalanche energy, single pulse $I_D = 5.5\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AS}$	340	mJ
Avalanche energy, repetitive $t_{AR}$ limited by $T_{jmax}$ <sup>1</sup> $I_D = 11\text{ A}$ , $V_{DD} = 50\text{ V}$	$E_{AR}$	0.6	
Avalanche current, repetitive $t_{AR}$ limited by $T_{jmax}$	$I_{AR}$	11	A
Gate source voltage	$V_{GS}$	$\pm 20$	V
Gate source voltage AC ( $f > 1\text{ Hz}$ )	$V_{GS}$	$\pm 30$	
Power dissipation, $T_C = 25\text{ }^\circ\text{C}$	$P_{tot}$	125	W
Operating and storage temperature	$T_j, T_{stg}$	-55... +150	$^\circ\text{C}$

**Maximum Ratings**

Parameter	Symbol	Value	Unit
Drain Source voltage slope $V_{DS} = 480\text{ V}$ , $I_D = 11\text{ A}$ , $T_j = 125\text{ °C}$	$dv/dt$	20	V/ns

**Thermal Characteristics**

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Thermal resistance, junction - case	$R_{thJC}$	-	-	1	K/W
Thermal resistance, junction - ambient, leaded	$R_{thJA}$	-	-	62	
SMD version, device on PCB: @ min. footprint @ 6 cm <sup>2</sup> cooling area <sup>2)</sup>	$R_{thJA}$	-	-	62	
Soldering temperature, 1.6 mm (0.063 in.) from case for 10s	$T_{sold}$	-	-	260	°C

**Electrical Characteristics, at  $T_j=25\text{ °C}$  unless otherwise specified**

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V$ , $I_D=0.25mA$	600	-	-	V
Drain-Source avalanche breakdown voltage	$V_{(BR)DS}$	$V_{GS}=0V$ , $I_D=11A$	-	700	-	
Gate threshold voltage	$V_{GS(th)}$	$I_D=500\mu A$ , $V_{GS}=V_{DS}$	3.5	4.5	5.5	
Zero gate voltage drain current	$I_{DSS}$	$V_{DS}=600V$ , $V_{GS}=0V$ , $T_j=25\text{ °C}$ , $T_j=150\text{ °C}$	-	-	25 250	$\mu A$
Gate-source leakage current	$I_{GSS}$	$V_{GS}=20V$ , $V_{DS}=0V$	-	-	100	
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V$ , $I_D=7A$ , $T_j=25\text{ °C}$ $T_j=150\text{ °C}$	-	0.34 0.92	0.38 -	$\Omega$
Gate input resistance	$R_G$	$f=1MHz$ , open Drain	-	29	-	

**Electrical Characteristics**, at  $T_j = 25\text{ °C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
<b>Characteristics</b>						
Transconductance	$g_{fs}$	$V_{DS} \geq 2 \cdot I_D \cdot R_{DS(on)max}$ , $I_D = 7A$	-	6	-	S
Input capacitance	$C_{iss}$	$V_{GS} = 0V$ , $V_{DS} = 25V$ , $f = 1MHz$	-	1460	-	pF
Output capacitance	$C_{oss}$		-	610	-	
Reverse transfer capacitance	$C_{rss}$		-	21	-	
Effective output capacitance, <sup>3)</sup> energy related	$C_{o(er)}$	$V_{GS} = 0V$ , $V_{DS} = 0V$ to $480V$	-	45	-	pF
Effective output capacitance, <sup>4)</sup> time related	$C_{o(tr)}$		-	85	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 350V$ , $V_{GS} = 0/10V$ , $I_D = 11A$ , $R_G = 6.8\Omega$	-	130	-	ns
Rise time	$t_r$		-	35	-	
Turn-off delay time	$t_{d(off)}$		-	150	225	
Fall time	$t_f$		-	20	30	

**Gate Charge Characteristics**

Gate to source charge	$Q_{gs}$	$V_{DD} = 350V$ , $I_D = 11A$	-	10.5	-	nC
Gate to drain charge	$Q_{gd}$		-	24	-	
Gate charge total	$Q_g$	$V_{DD} = 350V$ , $I_D = 11A$ , $V_{GS} = 0$ to $10V$	-	41.5	54	
Gate plateau voltage	$V_{(plateau)}$	$V_{DD} = 350V$ , $I_D = 11A$	-	8	-	V

<sup>1</sup> Repetitive avalanche causes additional power losses that can be calculated as  $P_{AV} = E_{AR} \cdot f$ .

<sup>2</sup> Device on 40mm\*40mm\*1.5mm epoxy PCB FR4 with 6cm<sup>2</sup> (one layer, 70 μm thick) copper area for drain connection. PCB is vertical without blown air.

<sup>3</sup>  $C_{o(er)}$  is a fixed capacitance that gives the same stored energy as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

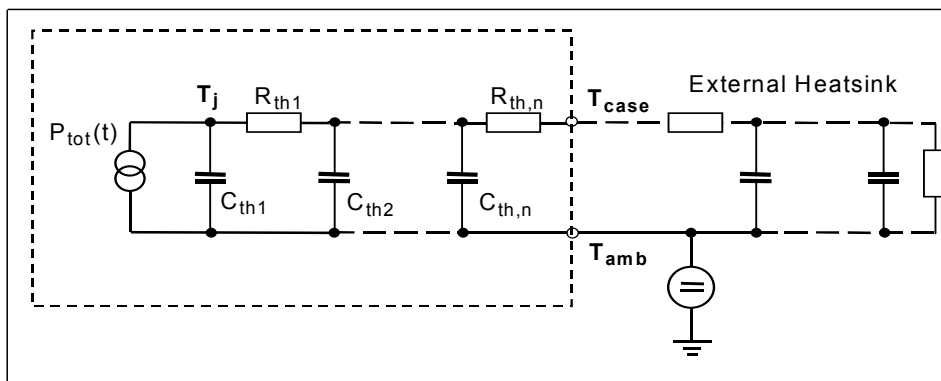
<sup>4</sup>  $C_{o(tr)}$  is a fixed capacitance that gives the same charging time as  $C_{oss}$  while  $V_{DS}$  is rising from 0 to 80%  $V_{DSS}$ .

**Electrical Characteristics**, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Inverse diode continuous forward current	$I_S$	$T_C=25^\circ\text{C}$	-	-	11	A
Inverse diode direct current, pulsed	$I_{SM}$		-	-	22	
Inverse diode forward voltage	$V_{SD}$	$V_{GS}=0\text{V}, I_F=I_S$	-	1	1.2	V
Reverse recovery time	$t_{rr}$	$V_R=350\text{V}, I_F=I_S,$	-	650	1105	ns
Reverse recovery charge	$Q_{rr}$	$di_F/dt=100\text{A}/\mu\text{s}$	-	7.9	-	$\mu\text{C}$

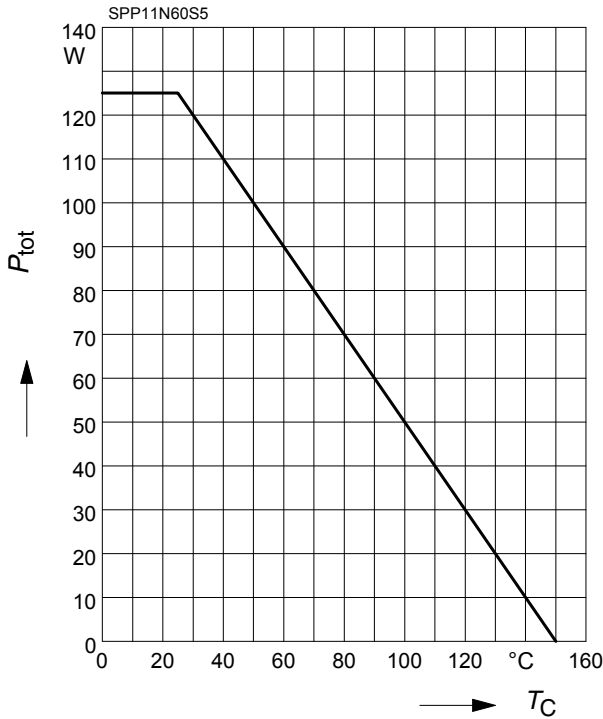
**Typical Transient Thermal Characteristics**

Symbol	Value	Unit	Symbol	Value	Unit
	typ.			typ.	
Thermal resistance			Thermal capacitance		
$R_{th1}$	0.015	K/W	$C_{th1}$	0.0001878	Ws/K
$R_{th2}$	0.03		$C_{th2}$	0.0007106	
$R_{th3}$	0.056		$C_{th3}$	0.000988	
$R_{th4}$	0.197		$C_{th4}$	0.002791	
$R_{th5}$	0.216		$C_{th5}$	0.007285	
$R_{th6}$	0.083		$C_{th6}$	0.063	



**1 Power dissipation**

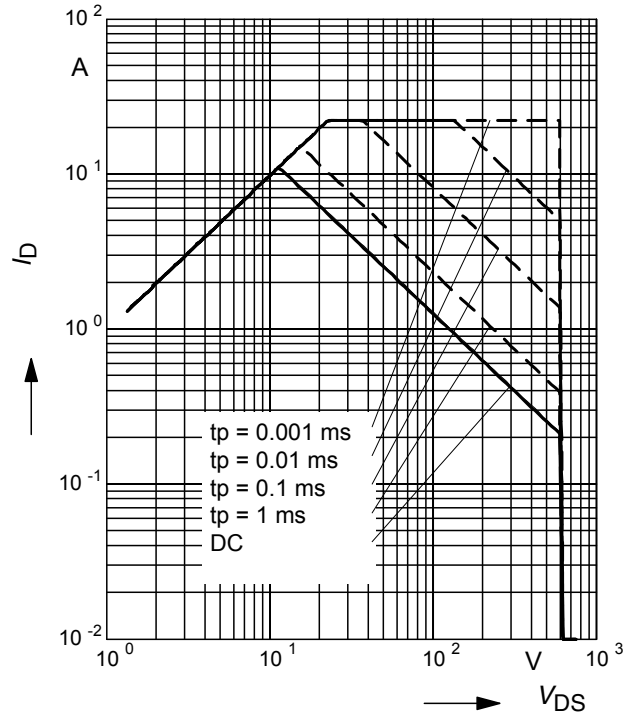
$P_{tot} = f(T_C)$



**2 Safe operating area**

$I_D = f(V_{DS})$

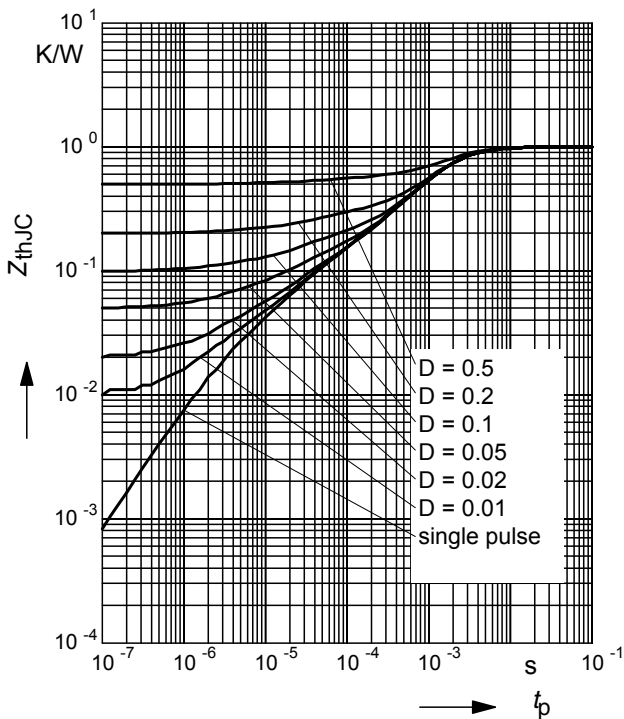
parameter :  $D = 0, T_C = 25^\circ C$



**3 Transient thermal impedance**

$Z_{thJC} = f(t_p)$

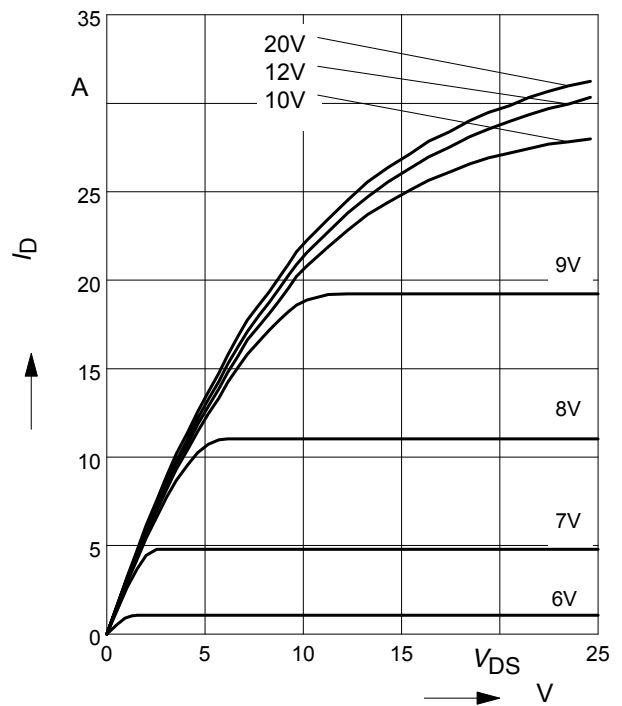
parameter:  $D = t_p/T$



**4 Typ. output characteristic**

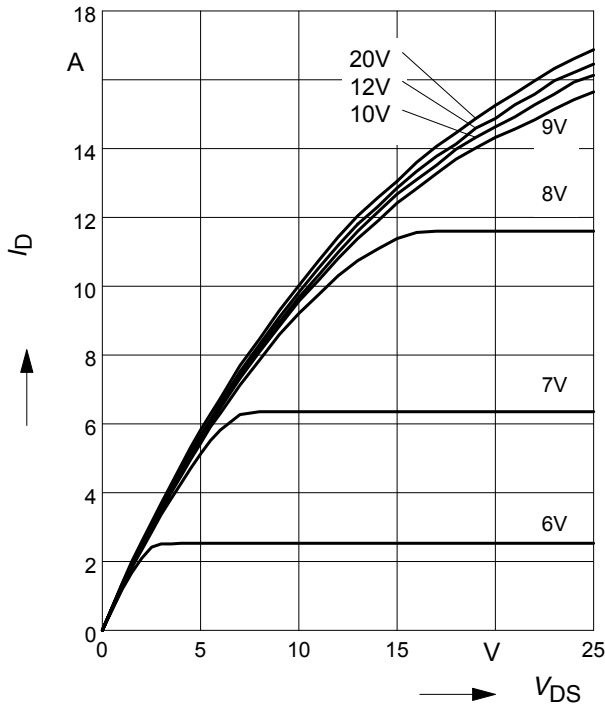
$I_D = f(V_{DS}); T_j = 25^\circ C$

parameter:  $t_p = 10 \mu s, V_{GS}$



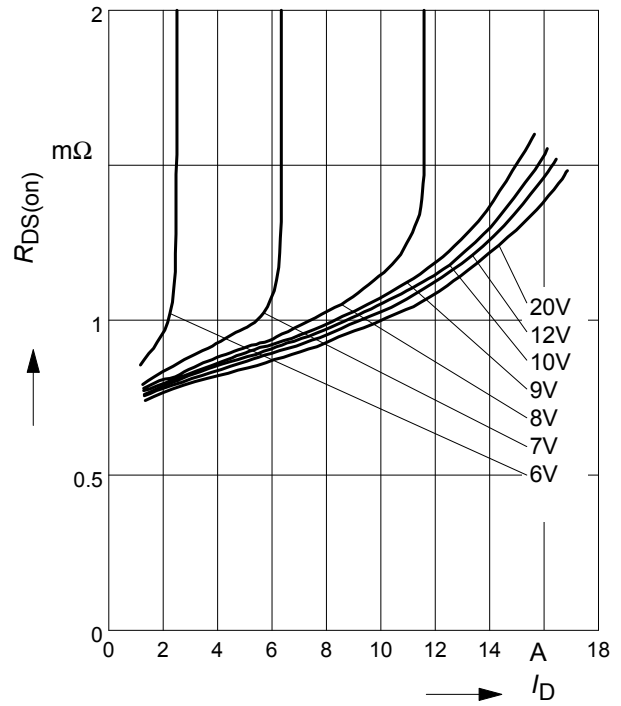
**5 Typ. output characteristic**

$I_D = f(V_{DS}); T_j = 150^\circ\text{C}$   
parameter:  $t_p = 10 \mu\text{s}, V_{GS}$



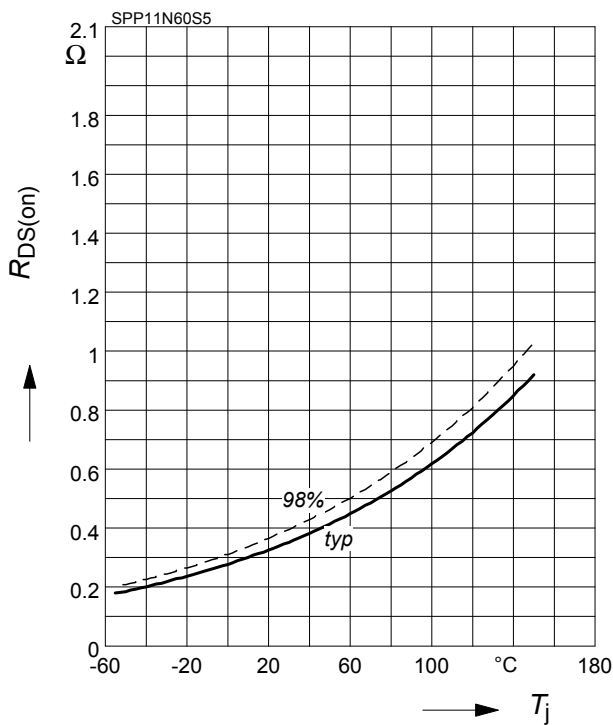
**6 Typ. drain-source on resistance**

$R_{DS(on)} = f(I_D)$   
parameter:  $T_j = 150^\circ\text{C}, V_{GS}$



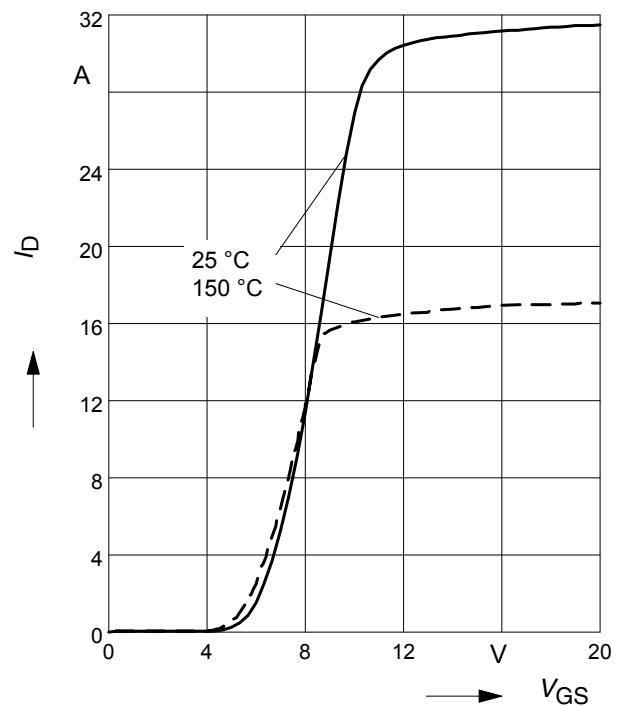
**7 Drain-source on-state resistance**

$R_{DS(on)} = f(T_j)$   
parameter:  $I_D = 7 \text{ A}, V_{GS} = 10 \text{ V}$



**8 Typ. transfer characteristics**

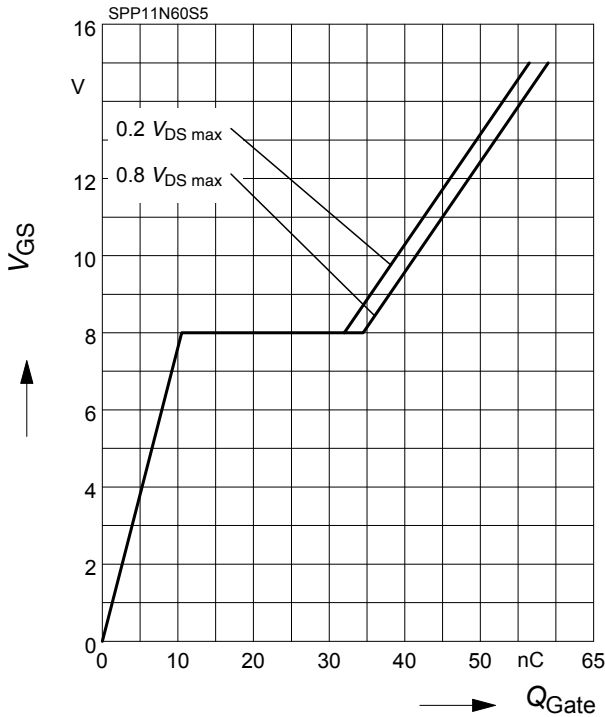
$I_D = f(V_{GS}); V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$   
parameter:  $t_p = 10 \mu\text{s}$



**9 Typ. gate charge**

$V_{GS} = f(Q_{Gate})$

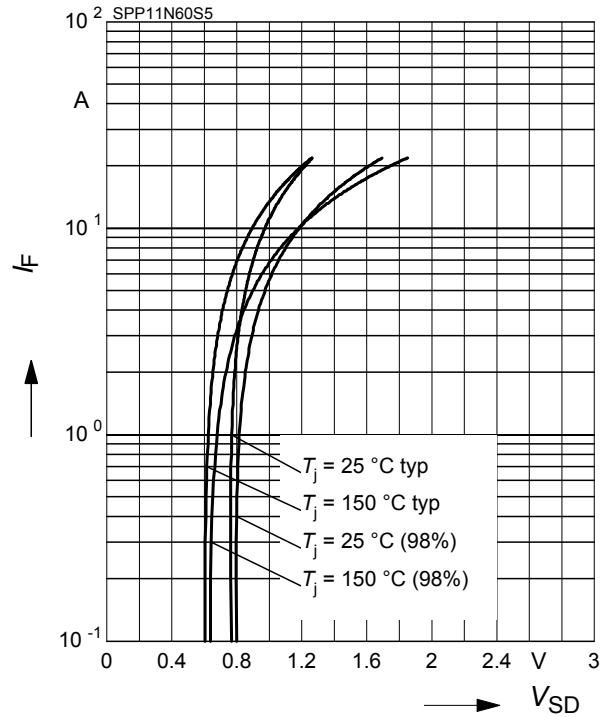
parameter:  $I_D = 11\text{ A}$  pulsed



**10 Forward characteristics of body diode**

$I_F = f(V_{SD})$

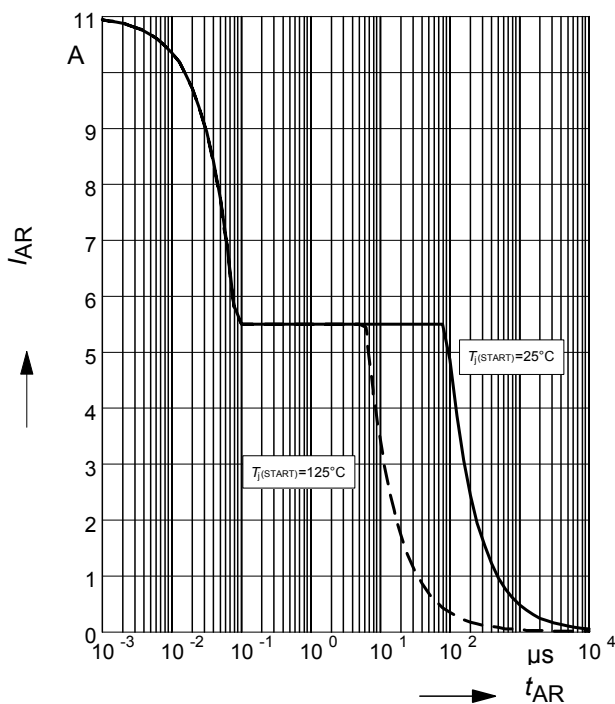
parameter:  $T_j, t_p = 10\ \mu\text{s}$



**11 Avalanche SOA**

$I_{AR} = f(t_{AR})$

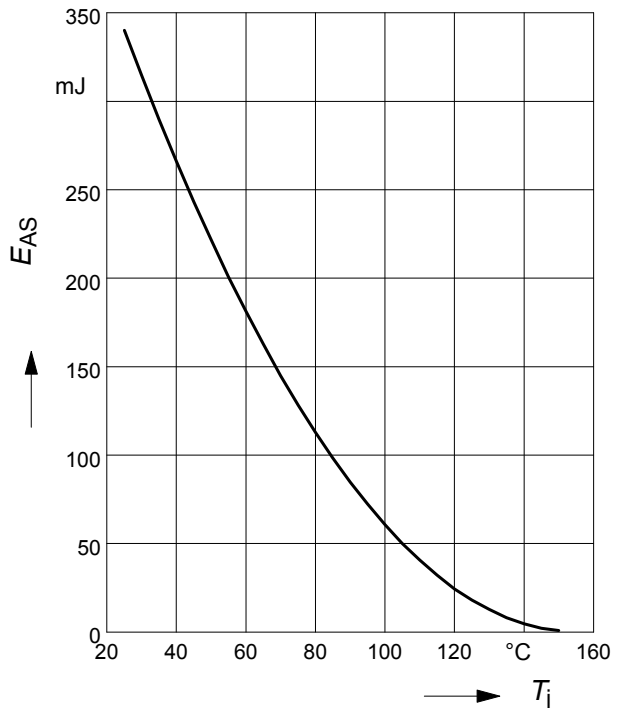
par.:  $T_j \leq 150\ \text{°C}$



**12 Avalanche energy**

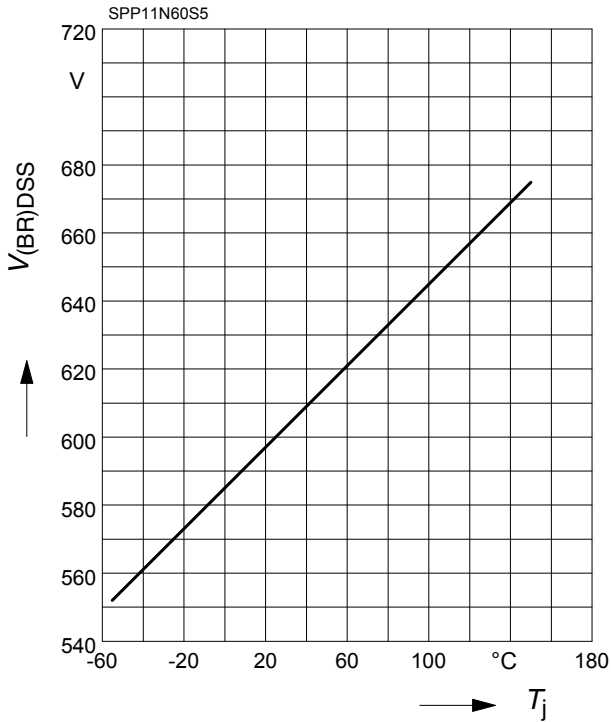
$E_{AS} = f(T_j)$

par.:  $I_D = 5.5\text{ A}, V_{DD} = 50\text{ V}$



**13 Drain-source breakdown voltage**

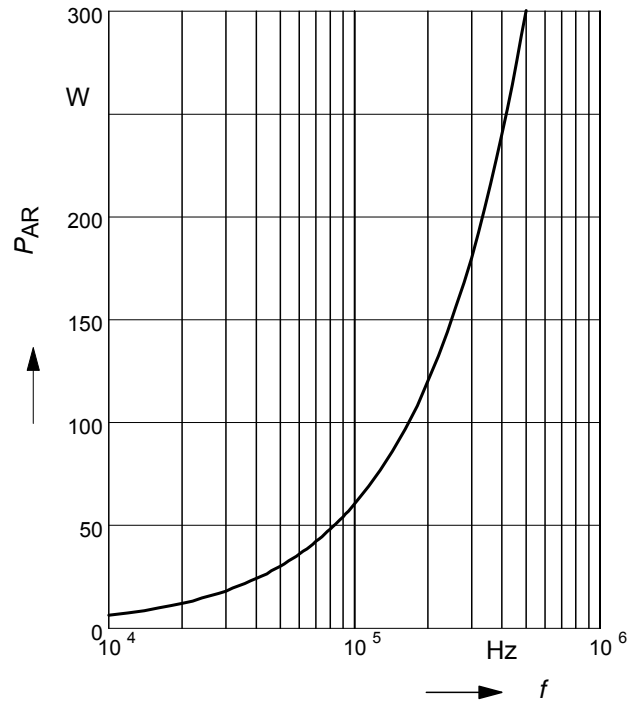
$$V_{(BR)DSS} = f(T_j)$$



**14 Avalanche power losses**

$$P_{AR} = f(f)$$

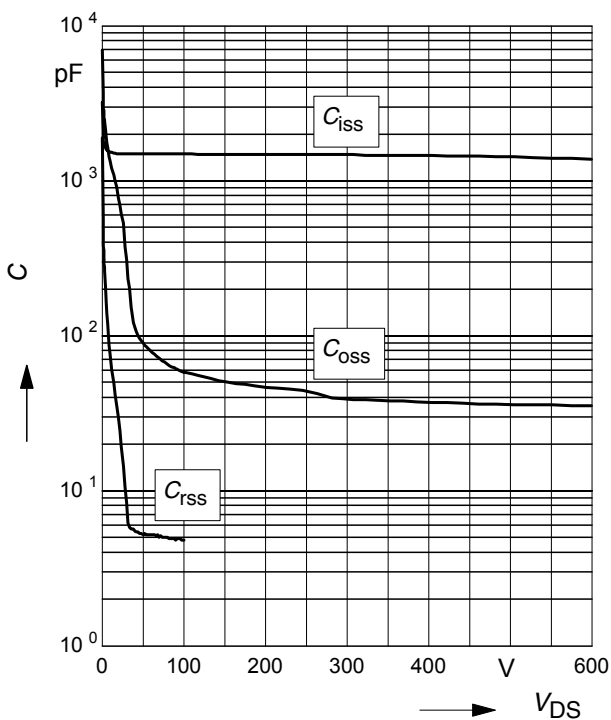
parameter:  $E_{AR}=0.6mJ$



**15 Typ. capacitances**

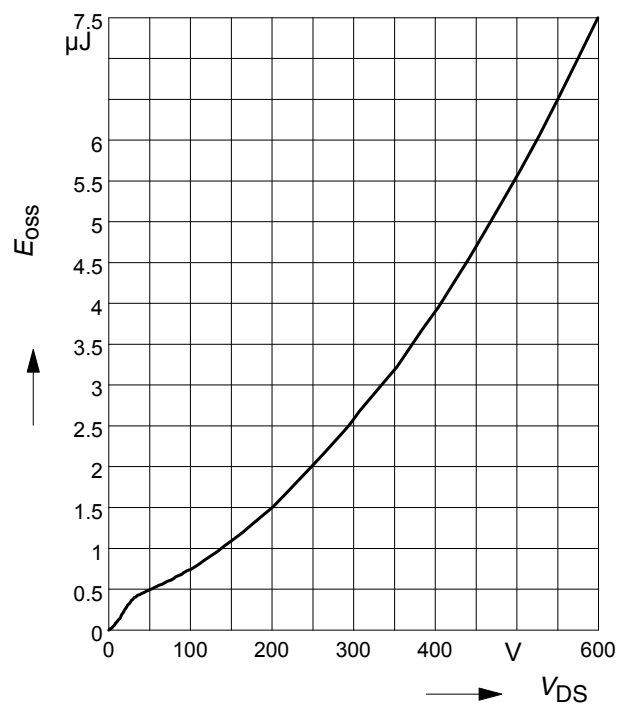
$$C = f(V_{DS})$$

parameter:  $V_{GS}=0V, f=1 MHz$



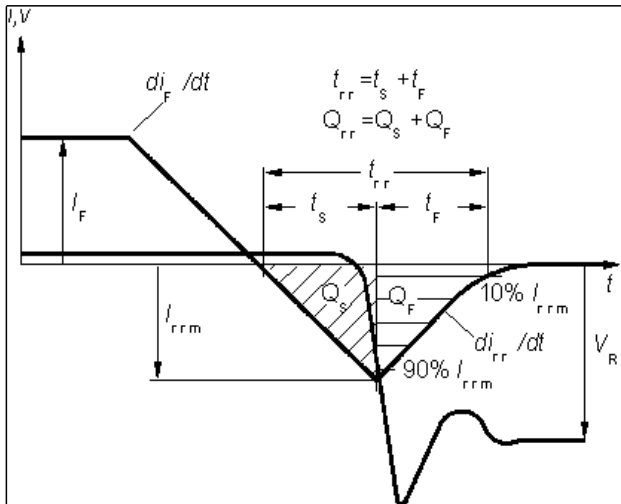
**16 Typ.  $C_{oss}$  stored energy**

$$E_{oss} = f(V_{DS})$$

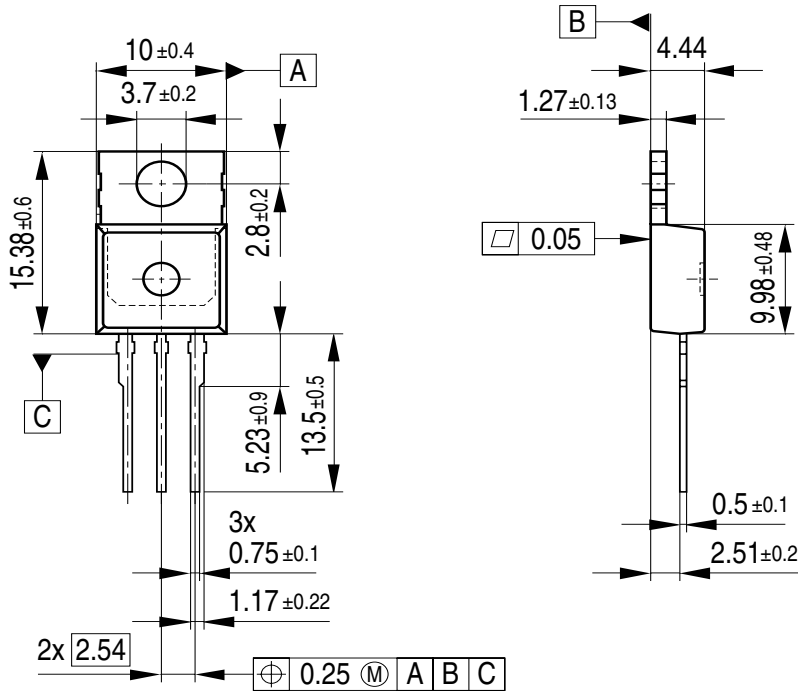




Definition of diodes switching characteristics

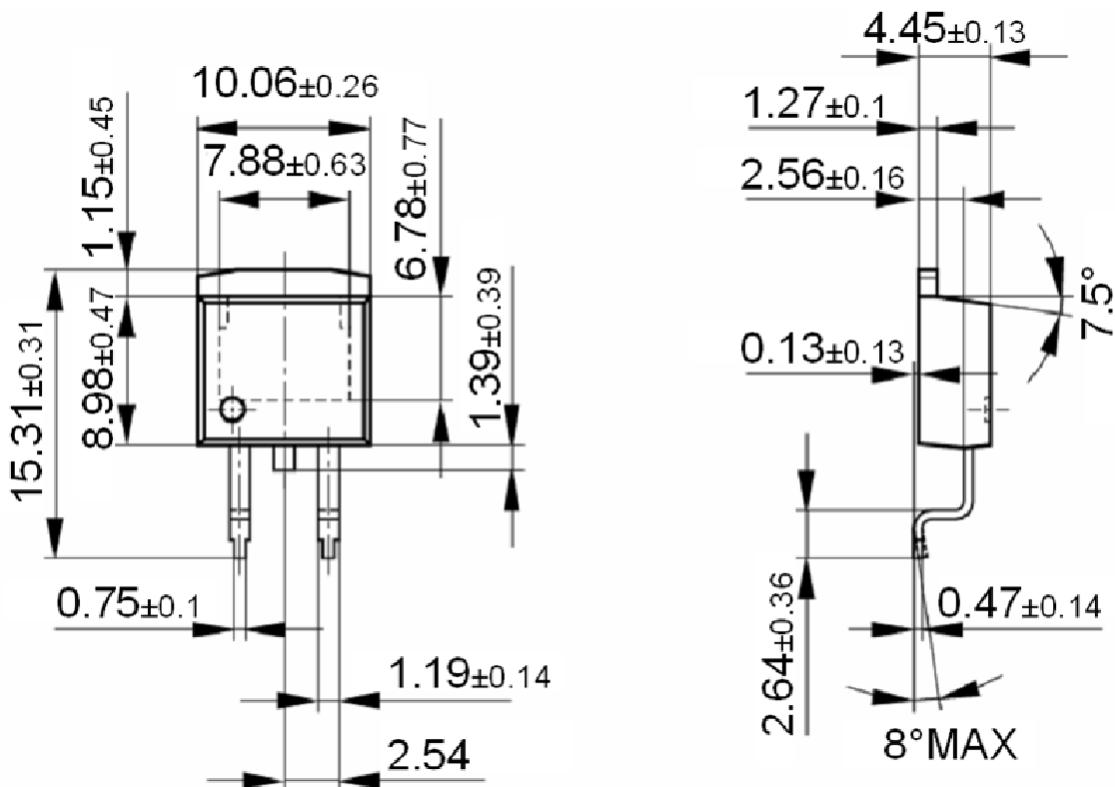


P-TO-220-3-1

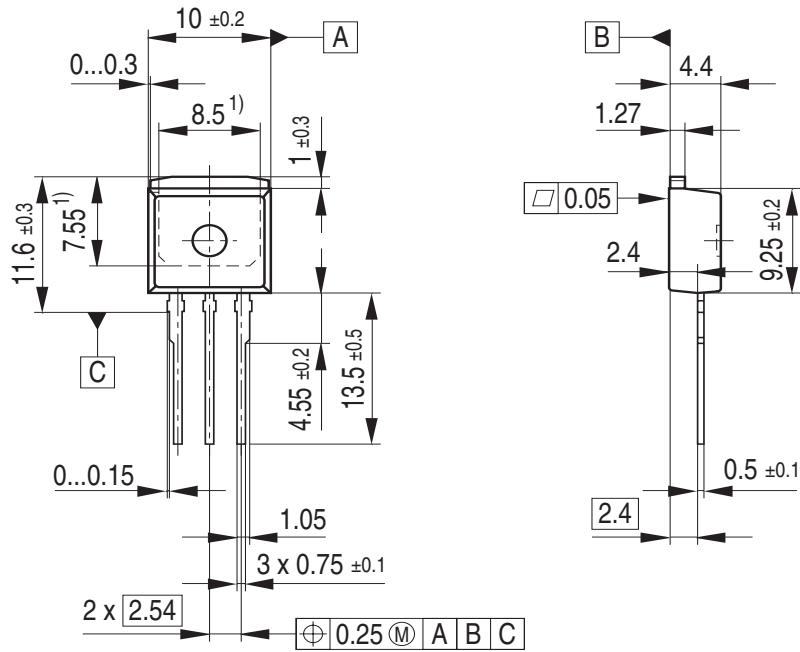


All metal surfaces tin plated, except area of cut.  
Metal surface min.  $x=7.25$ ,  $y=12.3$

P-TO-263-3-2 (D<sup>2</sup>PAK)



P-TO-262-3-1 (I<sup>2</sup>-PAK)



1) Typical

Metal surface min. X = 7.25, Y = 6.9

All metal surfaces tin plated, except area of cut.

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